

N-channel TrenchMOS intermediate level FET

Rev. 02 — 7 September 2010

Product data sheet

1. Product profile

1.1 General description

Intermediate level gate drive N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using advanced TrenchMOS technology. This product has been designed and qualified to the appropriate AEC Q101 standard for use in high performance automotive applications.

1.2 Features and benefits

- AEC Q101 compliant
- Suitable for intermediate level gate drive sources

1.3 Applications

- 12 V Automotive systems
- Electric and electro-hydraulic power steering
- Motors, lamps and solenoid control

1.4 Quick reference data

Table 1. Quick reference data

- Suitable for thermally demanding environments due to 175 °C rating
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

Parameter drain-source voltage drain current total power dissipation	Conditions $T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$ $V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C};$ see Figure 1 $T_{mb} = 25 \text{ °C};$ see Figure 2	[1]	Min - -	Typ - -	Max 30 120	Unit V A
voltage drain current total power	V _{GS} = 10 V; T _{mb} = 25 °C; see <u>Figure 1</u>	[1]	-	-		
total power	see Figure 1	<u>[1]</u>	-	-	120	А
	T _{mb} = 25 °C; see Figure 2					
ussipation			-	-	306	W
octeristics						
drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; see <u>Figure 16</u>		-	1.9	2.2	mΩ
ruggedness						
non-repetitive	$I_D = 120 \text{ A}; V_{sup} \le 30 \text{ V};$ $R_{GS} = 50 \Omega; V_{GS} = 10 \text{ V};$ $T_{idial} = 25 ^{\circ}\text{C}; \text{ unclamped}$		-	-	1.7	J
	uggedness non-repetitive drain-source	uggednessnon-repetitive $I_D = 120 \text{ A}; \text{ V}_{sup} \le 30 \text{ V};$ drain-source $R_{GS} = 50 \Omega; \text{ V}_{GS} = 10 \text{ V};$	uggedness non-repetitive $I_D = 120 \text{ A}; V_{sup} \le 30 \text{ V};$	uggednessnon-repetitive $I_D = 120 \text{ A}; \text{ V}_{sup} \le 30 \text{ V};$ drain-source $R_{GS} = 50 \Omega; \text{ V}_{GS} = 10 \text{ V};$	uggednessnon-repetitive $I_D = 120 \text{ A}; \text{ V}_{sup} \le 30 \text{ V};$ -drain-source $R_{GS} = 50 \Omega; \text{ V}_{GS} = 10 \text{ V};$	uggednessnon-repetitive $I_D = 120 \text{ A}; \text{ V}_{sup} \le 30 \text{ V};$ 1.7drain-source $R_{GS} = 50 \Omega; \text{ V}_{GS} = 10 \text{ V};$

[1] Continuous current is limited by package.

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2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	Drain	mb	
3	S	source		
	D			mbb076 S
			SOT226 (I2PAK)	

3. Ordering information

Table 3.Ordering information

Type number	Package		
	Name	Description	Version
BUK6E2R0-30C	I2PAK	plastic single-ended package (I2PAK); TO-262	SOT226

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4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Мах	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	30	V
V _{GS}	gate-source voltage		[1][2]	-16	16	V
			[3][4]	-20	20	V
I _D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see Figure 1	<u>[5]</u>	-	120	А
		T_{mb} = 100 °C; V_{GS} = 10 V; see Figure 1	<u>[5]</u>	-	120	А
I _{DM}	peak drain current	$T_{mb} = 25 \text{ °C}; t_p \le 10 \mu\text{s}; \text{ pulsed};$ see Figure 3		-	1082	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	306	W
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drai	n diode					
ls	source current	T _{mb} = 25 °C	[5]	-	120	А
I _{SM}	peak source current	$t_p \le 10 \ \mu s$; pulsed; $T_{mb} = 25 \ ^{\circ}C$		-	1082	А
Avalanche r	uggedness					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$\label{eq:ld} \begin{array}{l} I_{D} = 120 \; A; \; V_{sup} \leq 30 \; V; \; R_{GS} = 50 \; \Omega; \\ V_{GS} = 10 \; V; \; T_{j(init)} = 25 \; ^{\circ}C; \; unclamped \end{array}$		-	1.7	J
E _{DS(AL)R}	repetitive drain-source avalanche energy		<u>[6][7][8]</u>	-	-	J

[1] DC

[2] -16V accumulated duration not to exceed 168 hrs.

[3] Pulsed

[4] Accumulated pulse duration not to exceed 5mins.

[5] Continuous current is limited by package.

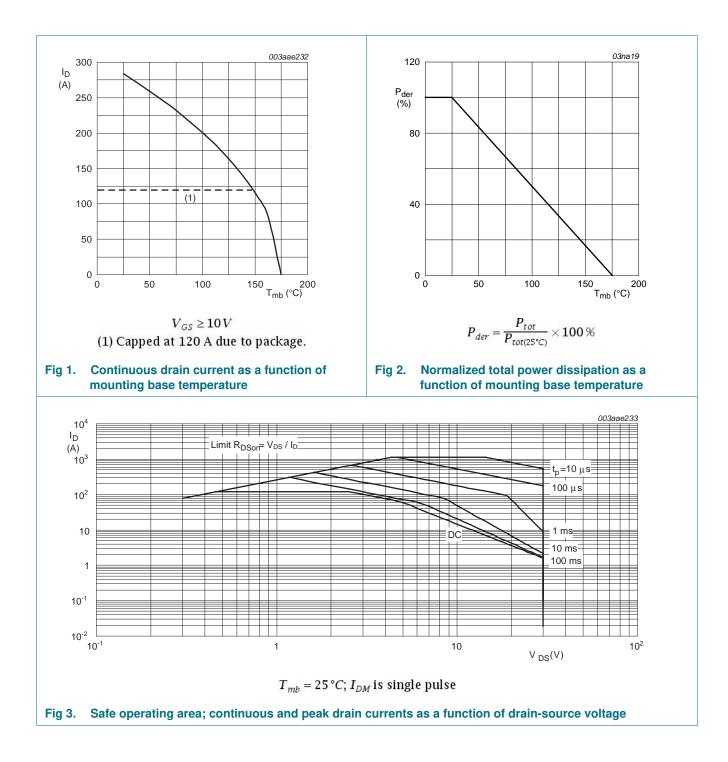
[6] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.

[7] Repetitive avalanche rating limited by an average junction temperature of 170 °C.

[8] Refer to application note AN10273 for further information.

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5. Thermal characteristics

	mermai enalacteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	-	0.49	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	vertical in free air	-	50	-	K/W

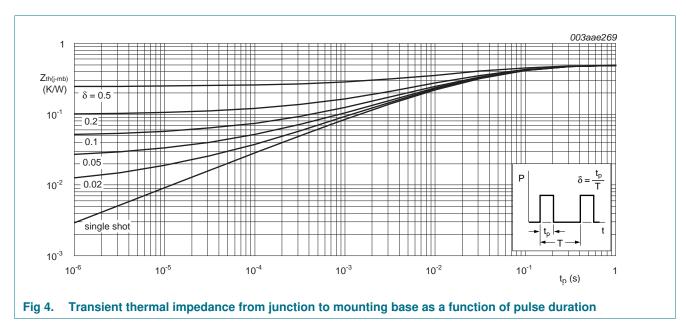


Table 5. Thermal characteristics

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6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics					
V _{(BR)DSS}	drain-source	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	30	-	-	V
	breakdown voltage	$I_D = 250 \ \mu A; V_{GS} = 0 \ V; T_j = -55 \ ^{\circ}C$	27	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 9</u> ; see <u>Figure 10</u>	1.8	2.3	2.8	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = -55 °C; see <u>Figure 10</u>	-	-	3.3	V
		I _D = 2.5 mA; V _{DS} = V _{GS} ; T _j = 175 °C; see <u>Figure 10</u>	0.8	-	-	V
I _{DSS}	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μA
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	1	μA
I _{GSS}	gate leakage current	$V_{DS} = 0 V; V_{GS} = 20 V; T_j = 25 \text{ °C}$	-	2	100	nA
		$V_{DS} = 0 \ V; \ V_{GS} = -20 \ V; \ T_j = 25 \ ^\circ C$	-	2	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; see <u>Figure 16</u>	-	1.9	2.2	mΩ
		V _{GS} = 5 V; I _D = 25 A; T _j = 25 °C; see <u>Figure 16</u>	-	2.3	3	mΩ
		V _{GS} = 4.5 V; I _D = 25 A; T _j = 25 °C; see <u>Figure 16</u>	-	2.6	3.7	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C; see <u>Figure 11</u> ; see <u>Figure 16</u>	-	3.4	4.2	mΩ
Dynamic ch	aracteristics					
Q _{G(tot)}	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 24 \text{ V}; V_{GS} = 5 \text{ V};$ see <u>Figure 12</u> ; see <u>Figure 13</u>	-	131	-	nC
		$I_D = 25 \text{ A}; V_{DS} = 24 \text{ V}; V_{GS} = 10 \text{ V};$	-	229	-	nC
Q _{GS}	gate-source charge	see Figure 12; see Figure 13	-	38	-	nC
Q _{GD}	gate-drain charge		-	63	-	nC
C _{iss}	input capacitance	$V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz;$	-	11223	14964	pF
C _{oss}	output capacitance	$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 14}{14}$	-	1780	2136	pF
C _{rss}	reverse transfer capacitance		-	1085	1486	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 25 \text{ V}; \text{R}_{L} = 1 \Omega; \text{V}_{GS} = 10 \text{ V}; \label{eq:VDS}$	-	53	-	ns
t _r	rise time	$R_{G(ext)} = 10 \ \Omega$	-	114	-	ns
t _{d(off)}	turn-off delay time		-	363	-	ns
t _f	fall time		-	192	-	ns
L _D	internal drain inductance	from drain lead 6 mm from package to centre of die ; $T_j = 25 \text{ °C}$	-	4.5	-	nH
L _S	internal source inductance	from source lead to source bond pad ; $T_i = 25 \text{ °C}$	-	7.5	-	nH

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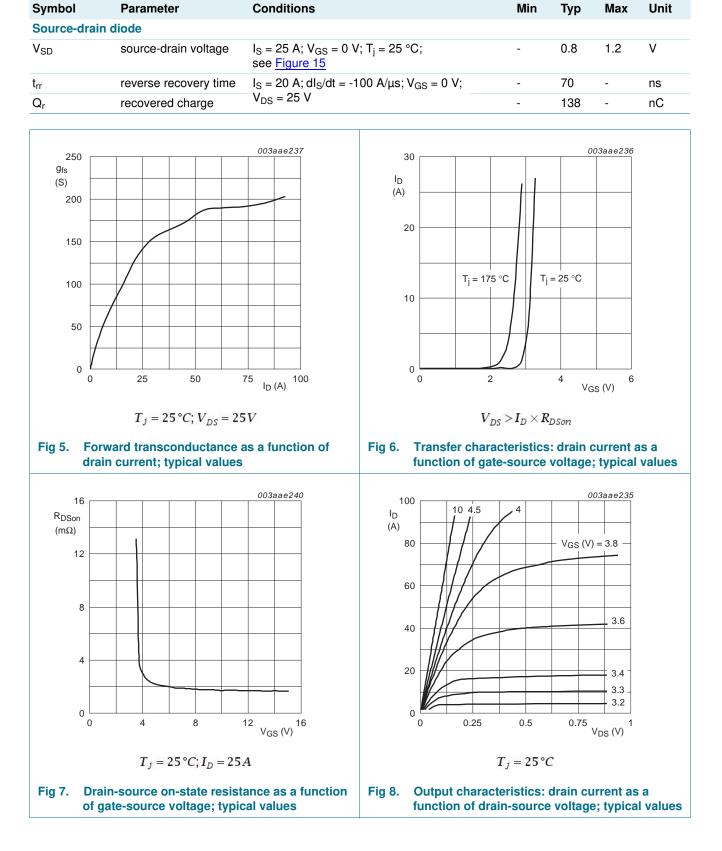
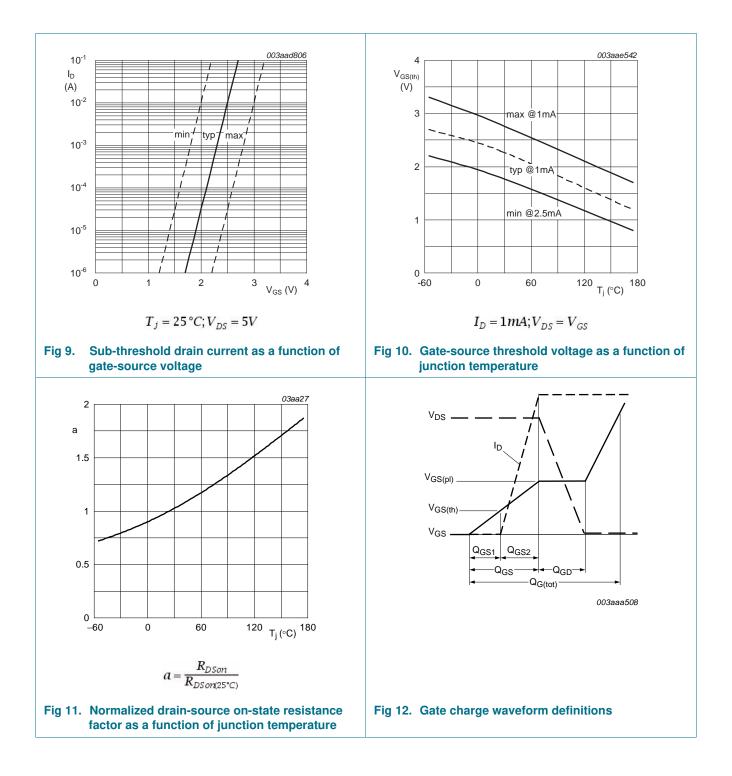


Table 6. Characteristics ...continued

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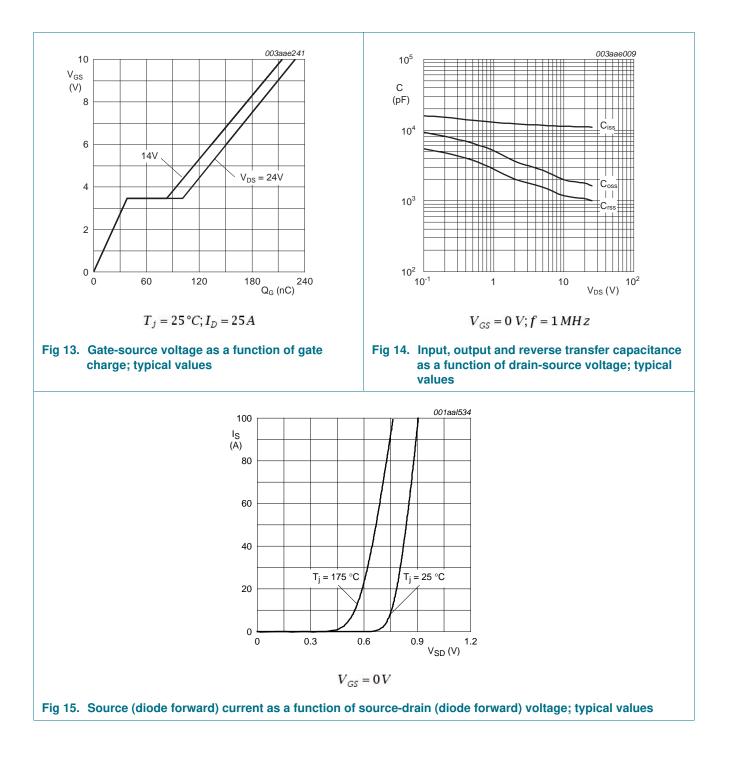
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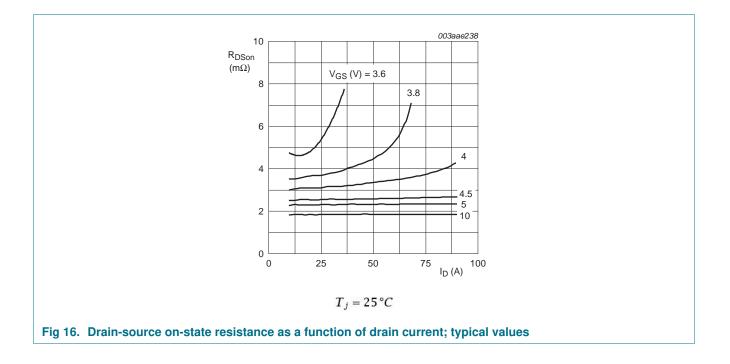
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7. Package outline

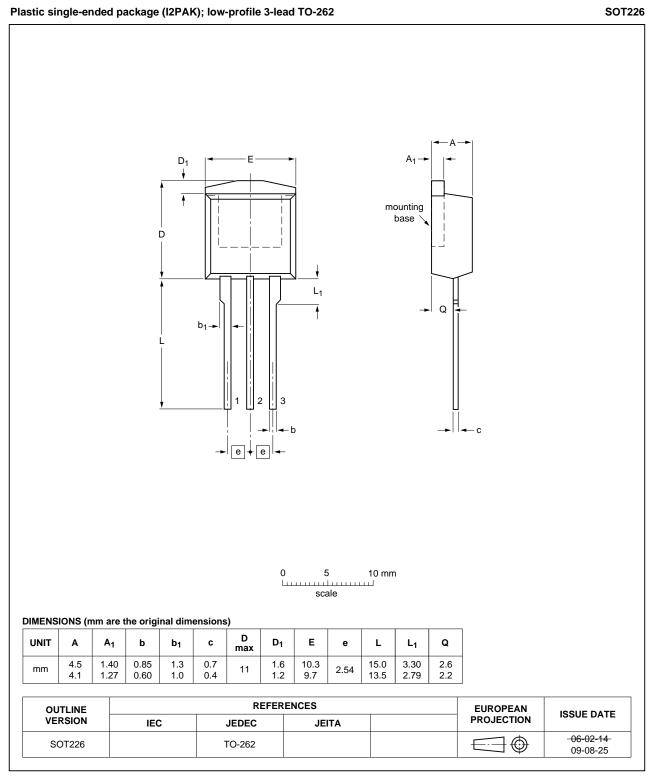


Fig 17. Package outline SOT226 (I2PAK)

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8. Revision history

Table 7. Revision h	nistory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK6E2R0-30C v.2	20100907	Product data sheet	-	BUK6E2R0-30C v.1
Modifications:	Various changes	s to content.		
BUK6E2R0-30C v.1	20100824	Product data sheet	-	-

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9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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